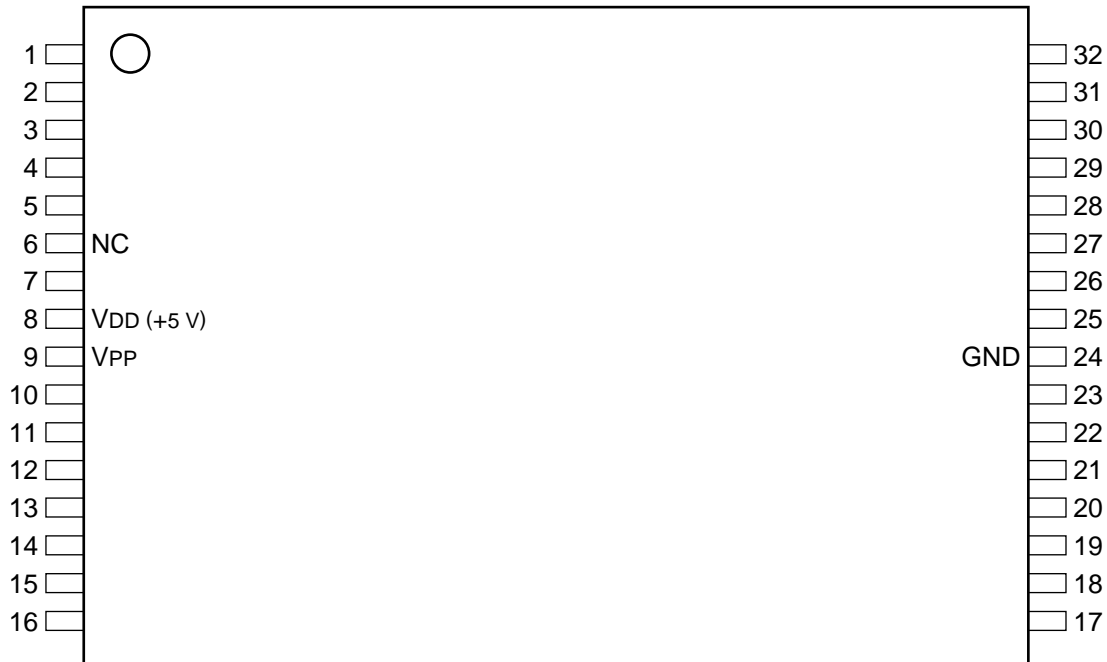
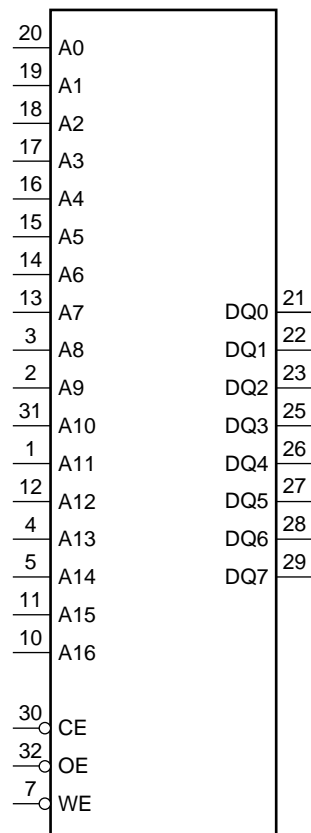


C-MOS 1M (131,072 × 8)-BIT BULK ERASE FLASH MEMORY

—TOP VIEW—

(V_{DD} = +5 V)

PIN NO.	I/O	SIGNAL	PIN NO.	I/O	SIGNAL
1	I	A11	17	I	A3
2	I	A9	18	I	A2
3	I	A8	19	I	A1
4	I	A13	20	I	A0
5	I	A14	21	I/O	DQ0
6	—	NC	22	I/O	DQ1
7	I	$\overline{\text{WE}}$	23	I/O	DQ2
8	—	V _{DD}	24	—	GND
9	—	V _{PP}	25	I/O	DQ3
10	I	A16	26	I/O	DQ4
11	I	A15	27	I/O	DQ5
12	I	A12	28	I/O	DQ6
13	I	A7	29	I/O	DQ7
14	I	A6	30	I	$\overline{\text{CE}}$
15	I	A5	31	I	A10
16	I	A4	32	I	$\overline{\text{OE}}$

INPUT

A0 - A16 : ADDRESS

 $\overline{\text{CE}}$: CHIP ENABLE $\overline{\text{OE}}$: OUTPUT ENABLE $\overline{\text{WE}}$: WRITE ENABLE**INPUT/OUTPUT**

DQ0 - DQ7 : DATA

OTHERV_{PP} : PROGRAM VOLTAGE

